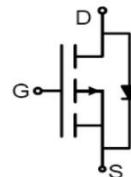


V_{DSS}	-200V
$R_{DS(on)}$	642m (typ.)
I_D	-6A



Advanced MOSFET process technology
 Special designed for PWM, load switching and
 general purpose applications
 Ultra low on-resistance with low gate charge
 Fast switching and reverse body recovery
 150 operating temperature



It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-6	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-4.2	
I_{DM}	Pulsed Drain Current	-24	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	75	W
V_{DS}	Drain-Source Voltage	-200	V
V_{GS}	Gate-to-Source Voltage	± 20	V
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

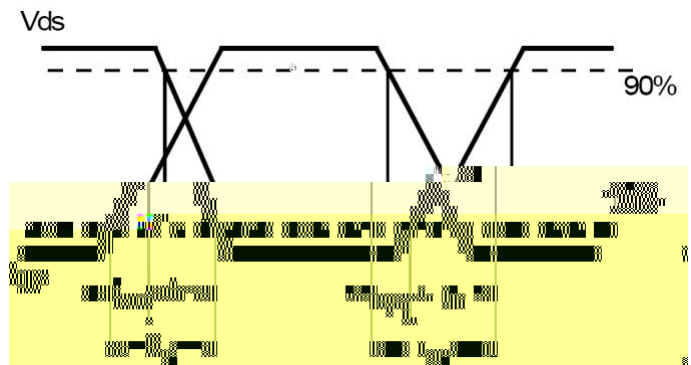
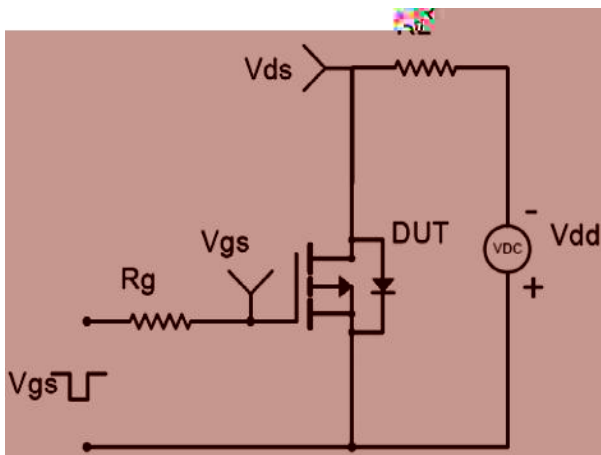
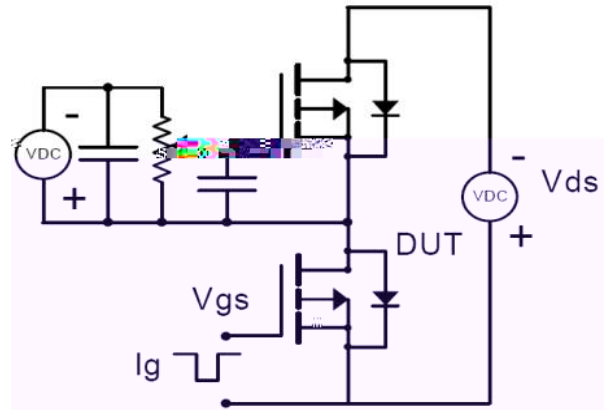
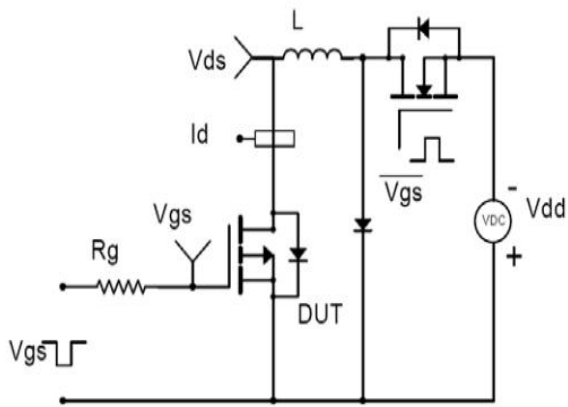


R _{JC}	Junction-to-case	—	2	/W

@T_A=25 unless otherwise specified

V _{(BR)DSS}	Drain-to-Source breakdown voltage	-200	—	—	V	V _{GS} = 0V, I _D = -250μA
R _{DS(on)}	Static Drain-to-Source on-resistance	—	642	834	m	V _{GS} =-10V, I _D =-2A
V _{GS(th)}	Gate threshold voltage	-2	—	-4	V	V _{DS} = V _{GS} , I _D =-250μA
I _{DSS}	Drain-to-Source leakage current	—	—	-1	μA	V _{DS} =-200V, V _{GS} = 0V
I _{GSS}	Gate-to-Source forward leakage	—	—	10		

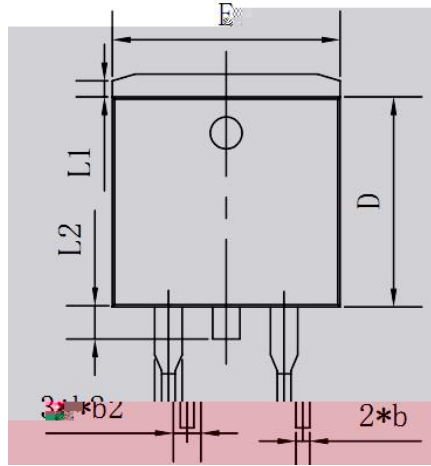
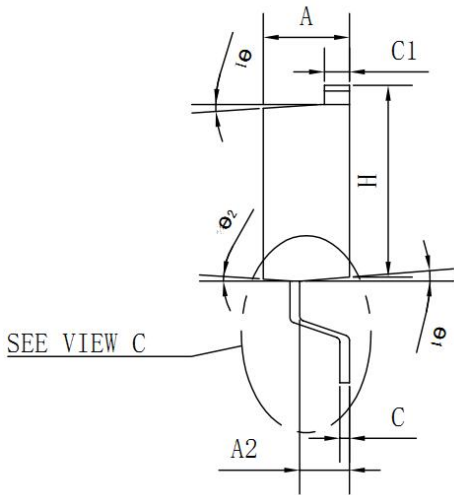
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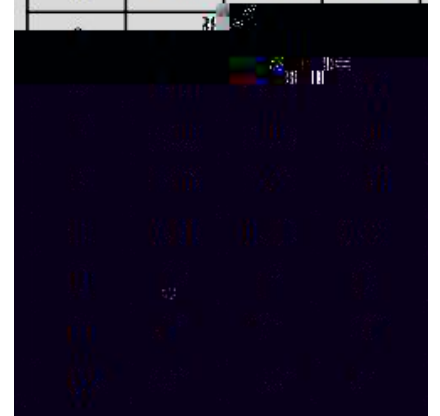
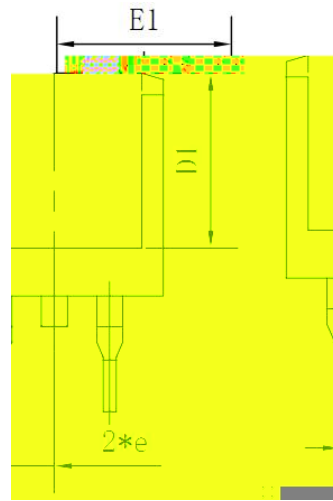
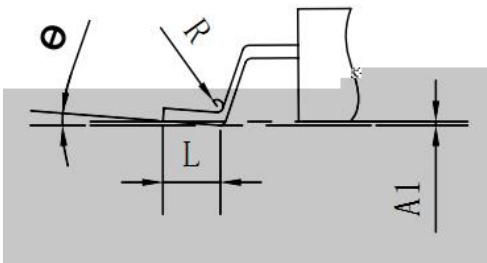
Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.



SYMBOL	MIN	NOM	MAX
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.50
b	0.70	0.80	1.00
b2	1.25	1.36	1.38
C	0.45	0.50	0.55
C1	1.29	1.30	1.31
D	9.10	9.20	9.30
D1	7.90	8.00	8.10
E	9.85	10.00	10.20
E1	7.90	8.00	8.10
H	15.30	15.50	15.70





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